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(71) Applicant: FUJITSU LTD

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(72) Inventor: NAKAMURA WATARU
O FUMIO
FUJIKI MITSUSHI

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(54) CAPACITIVE ELEMENT AND METHOD FOR
MANUFACTURING THE SAME

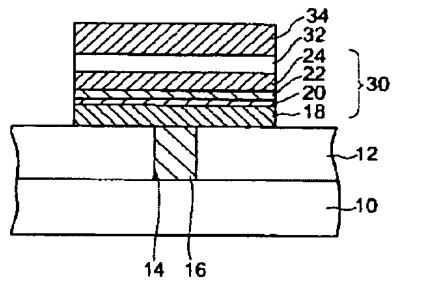
(57) Abstract:

本発明の第1実施形態による容量素子の構造を示す概略断面図

PROBLEM TO BE SOLVED: To provide a capacitive element having a ferroelectric film capable of preventing oxidation of a plug in a process for crystallizing a capacitor dielectric film in a stacked capacitive element, and preventing diffusion of iridium to the capacitor dielectric film.

SOLUTION: This capacitive element is provided with a lower electrode 30 constituted by successively forming first conductive films 18 and 20 including first metal, a second conductive film 22 formed on the first conductive films 18 and 20, and made of metallic oxide including second metal different from the first metal, and a third conductive film 24 formed on the second conductive film 22, and made of third metal different from the first metal.

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10 シリコン基板	22 酸化プラチナ膜
12 隔間絶縁膜	24 プラチナ膜
14 コンタクトホール	30 下部電極
16 ブラグ	32 キャパシタ誘電体膜
18 イリジウム膜	34 上部電極
20 酸化イリジウム膜	